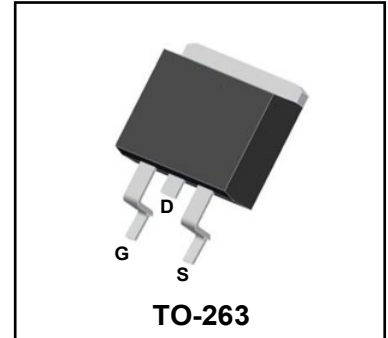


## 120V N-Channel Enhancement Mode Power MOSFET

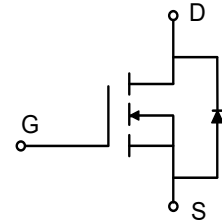
### Description

WMM036N12HGS uses Wayon's advanced power trench MOSFET technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance. This device is well suited for high efficiency fast switching applications.



### Features

- $V_{DS} = 120V$ ,  $I_D = 188A$   
 $R_{DS(on)} < 3.6m\Omega @ V_{GS} = 10V$
- Green Device Available
- Low Gate Charge
- 100% EAS Guaranteed



### Applications

- Synchronous Rectification
- DC/DC Converter
- Motor Control

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ , unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		$V_{DS}$	120	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_C = 25^\circ C$	$I_D$	188	A
	$T_C = 100^\circ C$		118	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	752	A
Single Pulse Avalanche Energy <sup>2</sup>		EAS	625	mJ
Total Power Dissipation	$T_C = 25^\circ C$	$P_D$	250	W
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	$^\circ C$

### Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>3</sup>	$R_{\theta JA}$	45	$^\circ C/W$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	0.5	$^\circ C/W$

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	120	-	-	V
Gate-body Leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$T_J = 25^\circ\text{C}$	$I_{DSS}$ $V_{DS} = 120V, V_{GS} = 0V$	-	-	1	$\mu A$
	$T_J = 100^\circ\text{C}$		-	-	100	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	3	3.5	V
Drain-Source on-Resistance <sup>4</sup>	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	-	2.9	3.6	m $\Omega$
Forward Transconductance <sup>4</sup>	$g_{fs}$	$V_{DS} = 10V, I_D = 20A$	-	77	-	S
<b>Dynamic Characteristics<sup>5</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 60V, V_{GS} = 0V,$ $f = 1\text{MHz}$	-	8690	-	$\mu F$
Output Capacitance	$C_{oss}$		-	733	-	
Reverse Transfer Capacitance	$C_{rss}$		-	16	-	
Gate Resistance	$R_g$	$f = 1\text{MHz}$	-	2.5	-	$\Omega$
<b>Switching Characteristics<sup>5</sup></b>						
Total Gate Charge	$Q_g$	$V_{GS} = 10V, V_{DS} = 60V,$ $I_D = 20A$	-	144	-	nC
Gate-Source Charge	$Q_{gs}$		-	38	-	
Gate-Drain Charge	$Q_{gd}$		-	37	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 60V,$ $R_G = 3\Omega, I_D = 20A$	-	29.6	-	ns
Rise Time	$t_r$		-	50.6	-	
Turn-off Delay Time	$t_{d(off)}$		-	89	-	
Fall Time	$t_f$		-	54	-	
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20A, dI/dt = 100A/\mu s$	-	90	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	217	-	nC
<b>Drain-Source Body Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$I_S = 20A, V_{GS} = 0V$	-	-	1.2	V
Continuous Source Current	$I_S$	$T_C = 25^\circ\text{C}$	-	-	188	A

## Notes:

1. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ\text{C}$ .
2. The test condition is  $V_{DD} = 55V, V_{GS} = 10V, L = 0.5\text{mH}, I_{AS} = 50A$ .
3. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

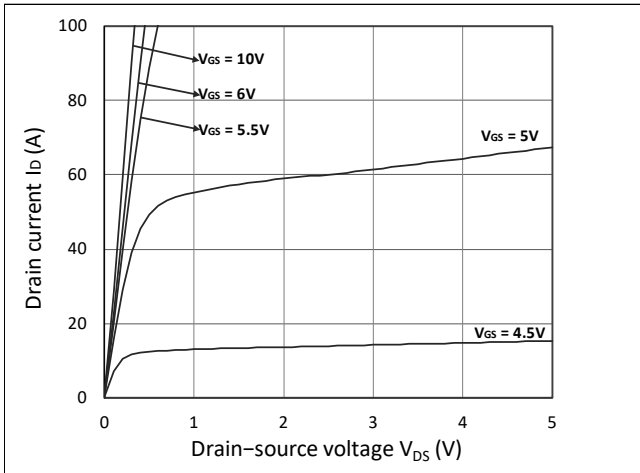


Figure 1. Output Characteristics

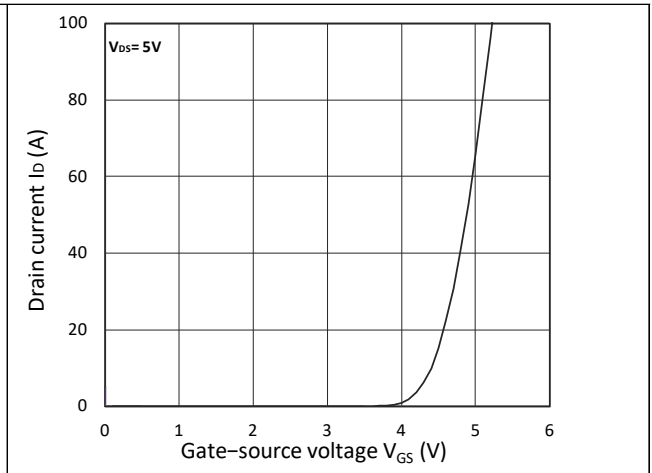


Figure 2. Transfer Characteristics

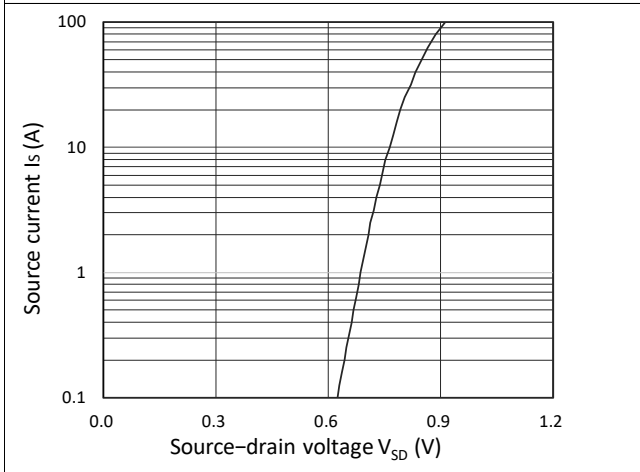


Figure 3. Forward Characteristics of Reverse

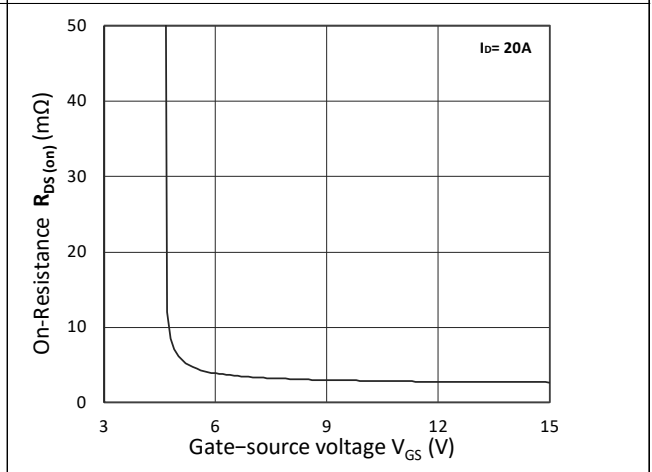


Figure 4.  $R_{DS(ON)}$  vs.  $V_{GS}$

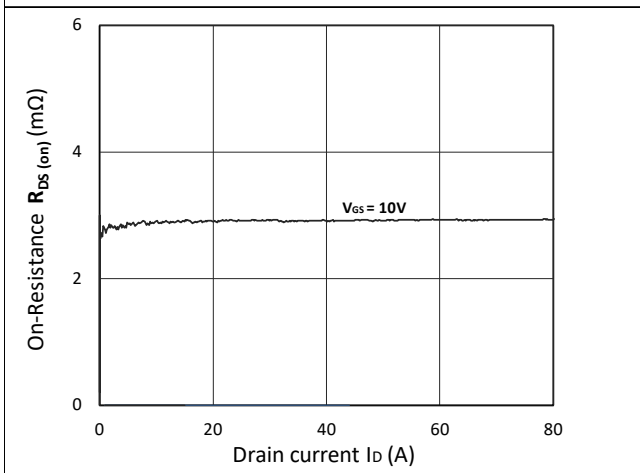


Figure 5.  $R_{DS(ON)}$  vs.  $I_D$

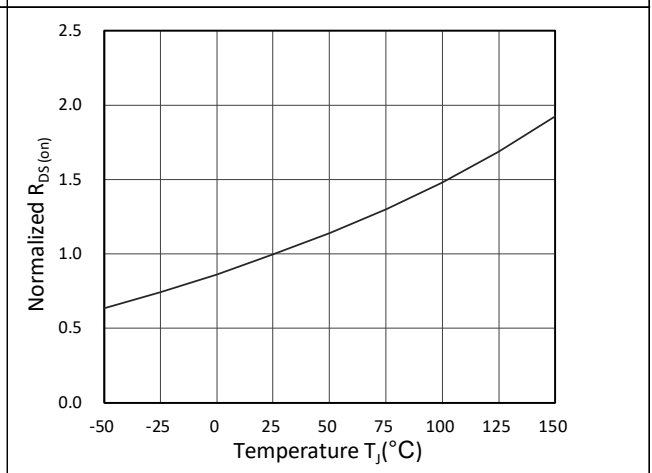


Figure 6. Normalized  $R_{DS(ON)}$  vs. Temperature

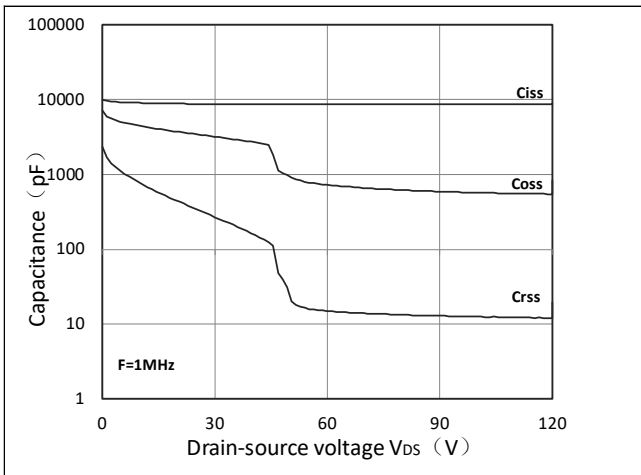


Figure 7. Capacitance Characteristics

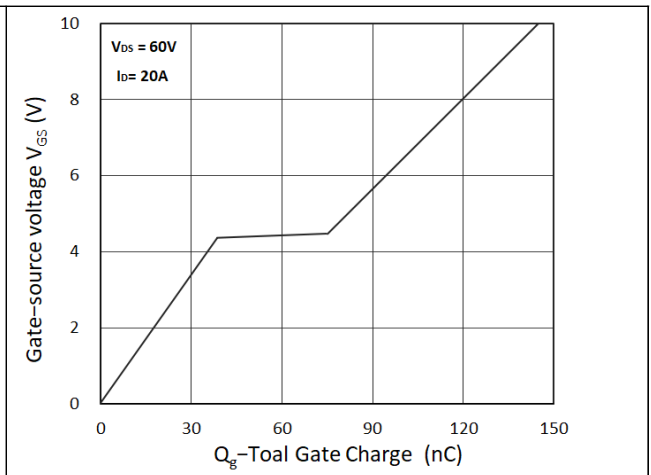


Figure 8. Gate Charge Characteristics

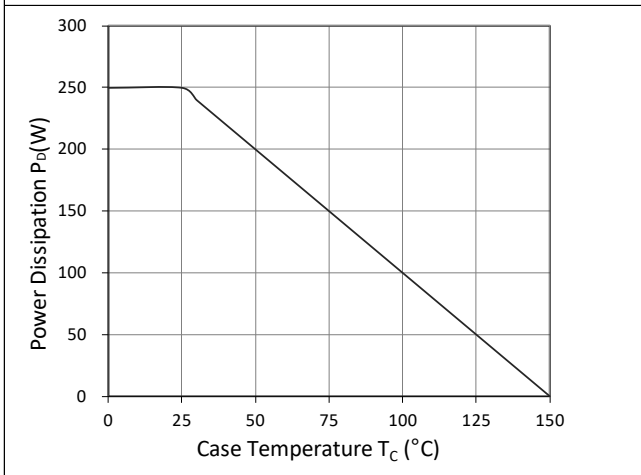


Figure 9. Power Dissipation

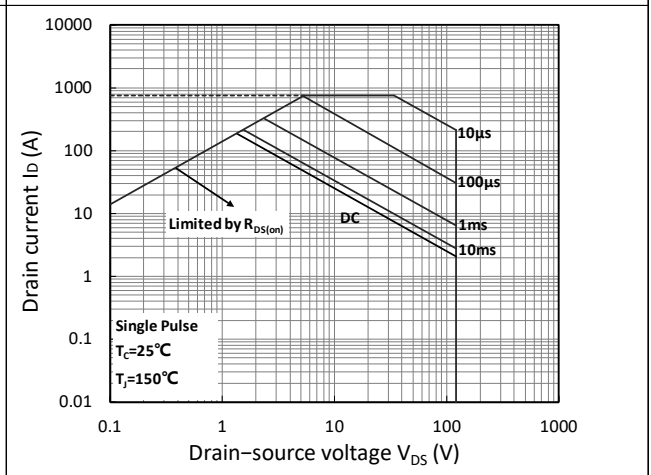


Figure 10. Safe Operating Area

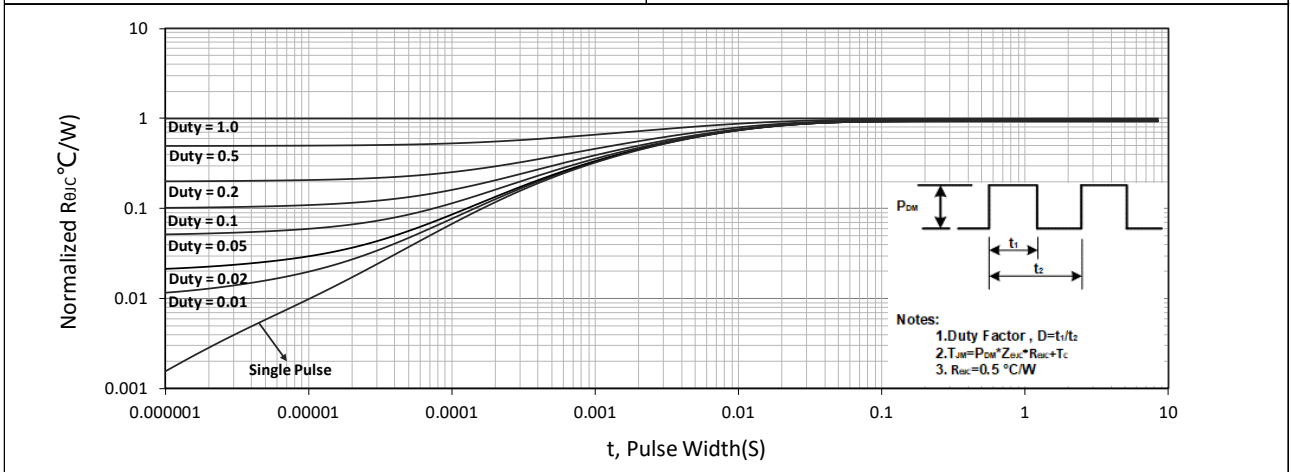


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

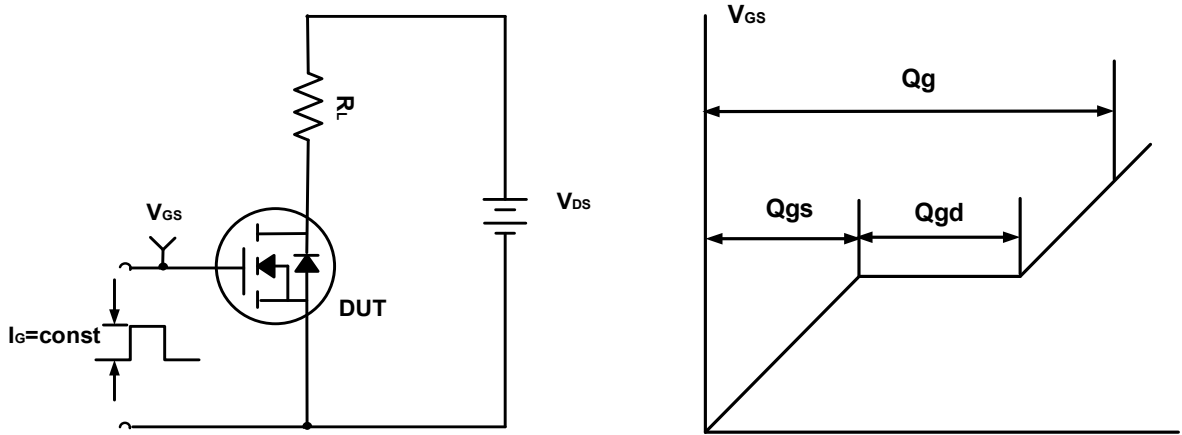


Figure A. Gate Charge Test Circuit & Waveforms

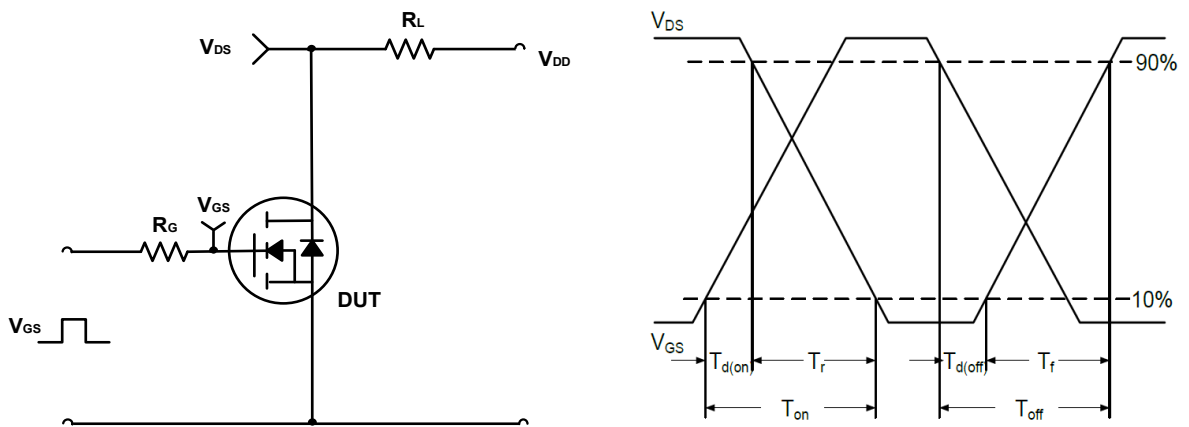


Figure B. Switching Test Circuit & Waveforms

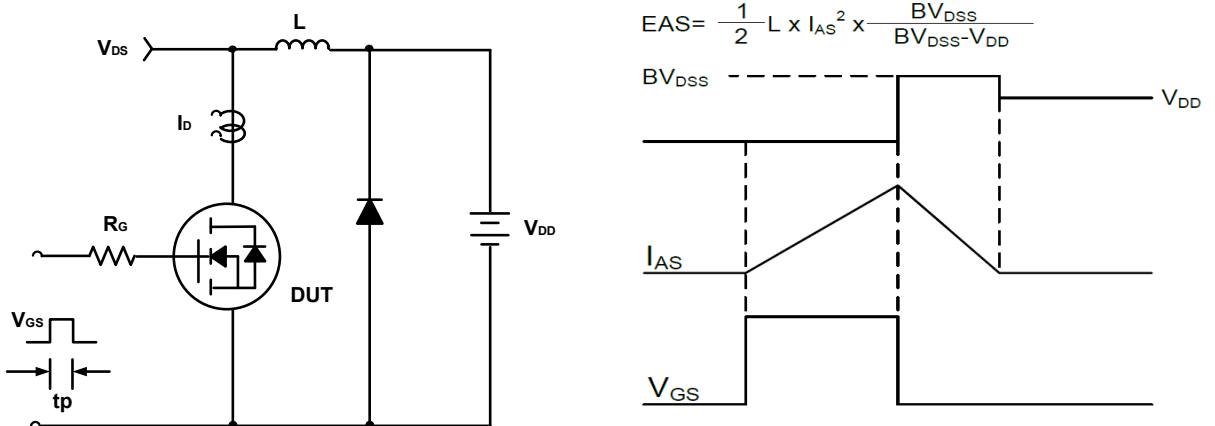
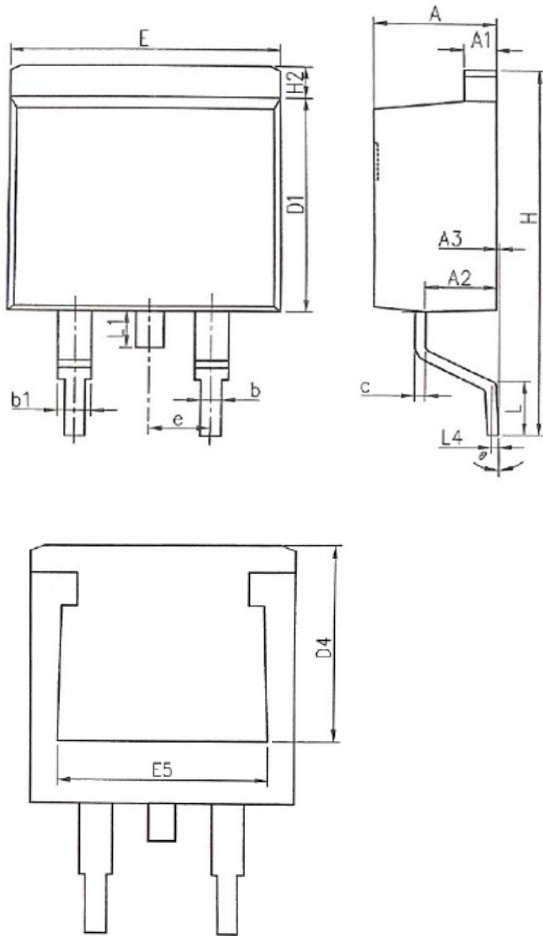


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for TO-263

COMMON DIMENSIONS

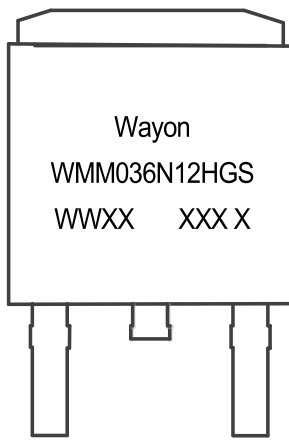


SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°

## Ordering Information

Part	Package	Marking	Packing method
WMM036N12HGS	TO-263	WMM036N12HGS	Tape and Reel

## Marking Information



WMM036N12HGS = Device code

WWXX XXX X= Date code


## Contact Information

No.1001, Shiwan(7) Road, Pudong District, Shanghai, P.R.China.201207

Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

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